Jacques *et al.* Reply: The authors of [1] give interesting suggestions to explain the unusual dissociation width reported in [2]. Glide processes due to ''large applied stresses on pinned dislocations'' are indeed not in agreement with the experimental conditions. However, the explanation for the large dissociation width related to the ''specific treatment that introduces dislocations in the sample'' seems appropriate. Indeed, the sample studied in this Letter is very different from pure silicon. In order to prove the efficiency of the coherent x-ray diffraction method, one had to find a perfect sample containing only a few dislocation loops, far away from each other and large enough in diameter to be seen by topography. Such systems are not so common, and this annealed silicon sample fulfils all the necessary conditions. This very peculiar growth process, in an oxygen atmosphere, at 1200 °C, stabilizes larger dislocation loops (100 microns in diameter) than usual [3]. They were observed by x-ray topography, and it would be highly interesting to study them with TEM.

Thus, the dissociation width found in our work on an annealed silicon sample cannot be generalized to pure silicon.

V. L. R. Jacques,[1,*] S. Ravy,[2] D. Le Bolloc'h,[3] E. Pinsolle,[3,2] M. Sauvage-Simkin,[2] and F. Livet[4]
[1]European Synchrotron Radiation Facility
6 rue Jules Horowitz, BP220
38043 Grenoble Cedex, France
[2]Synchrotron SOLEIL
L'Orme des merisiers
Saint-Aubin BP 48, 91192 Gif-sur-Yvette cedex, France
[3]Laboratoire de Physique des Solides (CNRS-UMR 8502)
Bâtiment 510
Université Paris-sud
91405 Orsay cedex, France
[4]Sciences et Ingénierie des Matériaux et Procédés
INP Grenoble CNRS UJF
BP 75, 38402 St Martin d'Hères Cedex, France

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*vjacques@esrf.fr

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